

## Features

- Low On-Resistance:
  - $R_{DS(ON)} < 54m\Omega @ V_{GS} = 10V$
  - $R_{DS(ON)} < 72m\Omega @ V_{GS} = 4.5V$
  - $R_{DS(ON)} < 115m\Omega @ V_{GS} = 2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

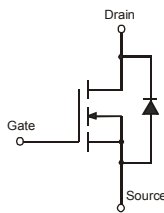
## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

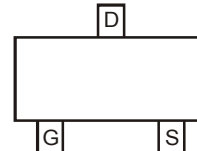
SOT-23



TOP VIEW



EQUIVALENT CIRCUIT



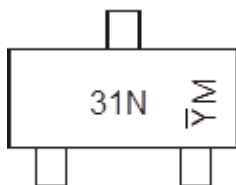
Pin Configuration

## Ordering Information (Note 4)

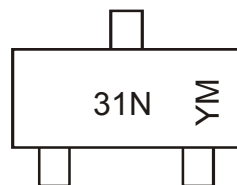
Part Number	Case	Packaging
DMN3150L-7	SOT-23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

## Marking Information



Chengdu A/T Site



Shanghai A/T Site

31N = Product Type Marking Code  
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)  
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)  
 Y or Y̅ = Year (ex: A = 2013)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018
Code	W	X	Y	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	I <sub>D</sub>	T <sub>A</sub> = +25°C	3.8
		T <sub>A</sub> = +70°C	3.1
Drain Current (Note 5)	I <sub>DM</sub>	15	A
Body-Diode Continuous Current (Note 5)	I <sub>S</sub>	2.0	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	800	nA	V <sub>DS</sub> = 28V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±80 ±800	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±19V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.62	0.92	1.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	39	54	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.8A
		—	52	72		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A
			90	115		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.1A
Forward Transconductance	Y <sub>fs</sub>	—	3	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 3.1A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	—	—	1.16	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.0A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Gate Resistance	R <sub>g</sub>	-	4.17	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (10V)	Q <sub>g</sub>	-	8.2	-	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.8A
Total Gate Charge (4.5V)	Q <sub>g</sub>	-	3.7	-	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.8A
Gate-Source Charge	Q <sub>gs</sub>	-	0.7	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	1.1	-	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	1.14	-	ns	V <sub>DD</sub> = 15V, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 6Ω, R <sub>L</sub> = 3.9Ω
Turn-On Rise Time	t <sub>r</sub>	-	3.49	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	15.02	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	3.26	-	ns	
Input Capacitance	C <sub>iss</sub>	—	305	—	pF	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	74	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	48	—	pF	

- Notes:
5. Device mounted on FR-4 PCB. t ≤ 5 sec.
  6. Short duration pulse test used to minimize self-heating effect.
  7. Guaranteed by design. Not subject to production testing.

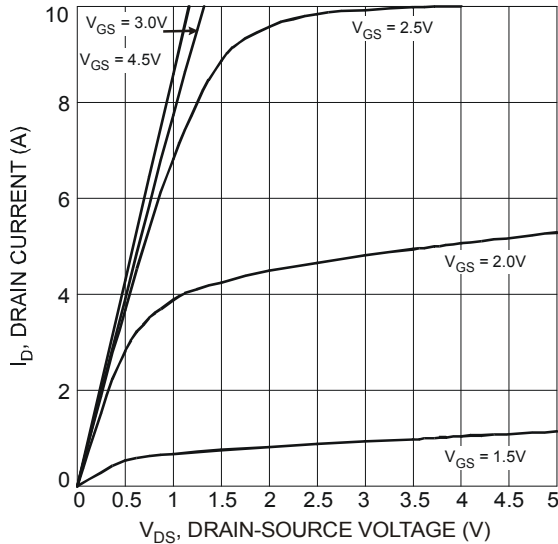


Fig. 1 Typical Output Characteristics

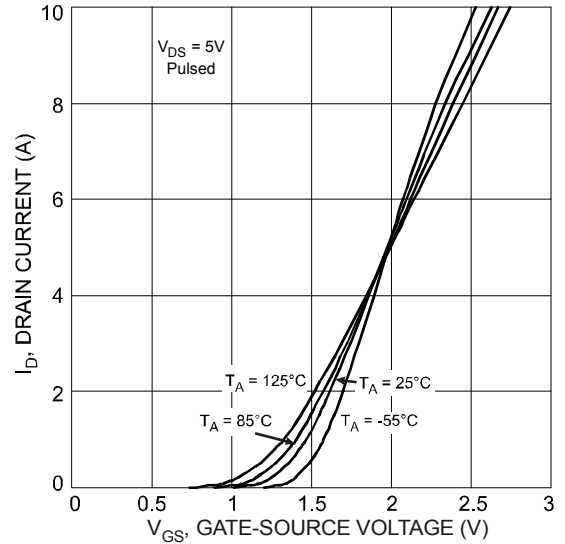


Fig. 2 Typical Transfer Characteristics

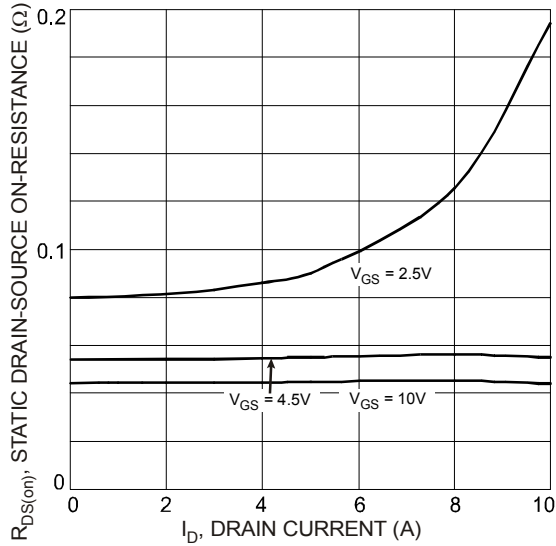


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

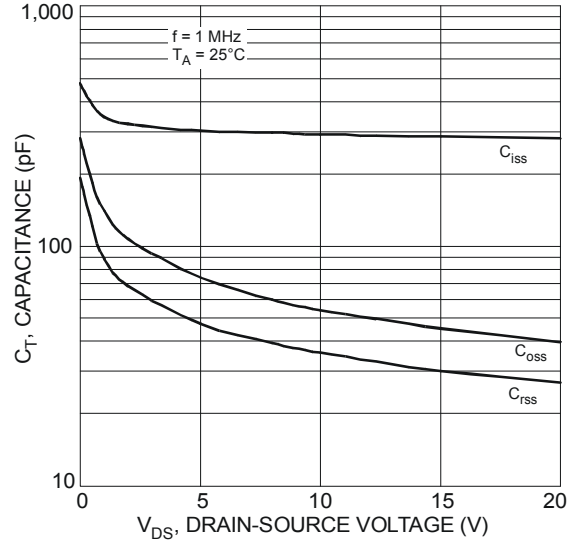


Fig. 4 Typical Total Capacitance

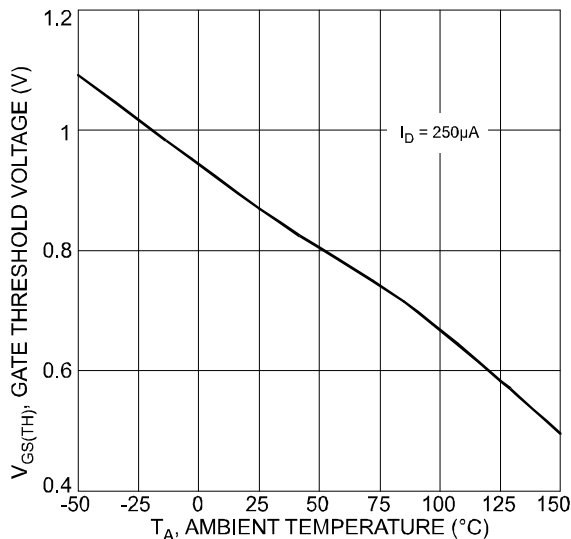


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

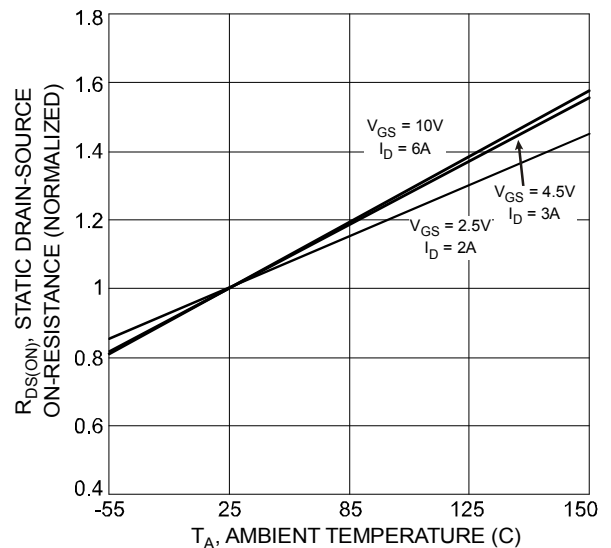


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

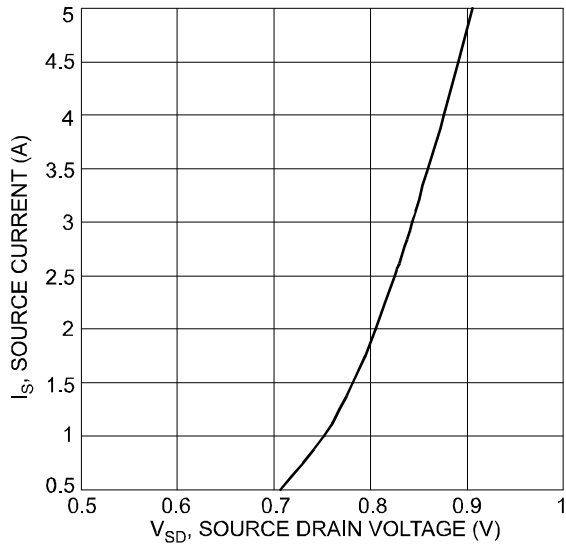


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

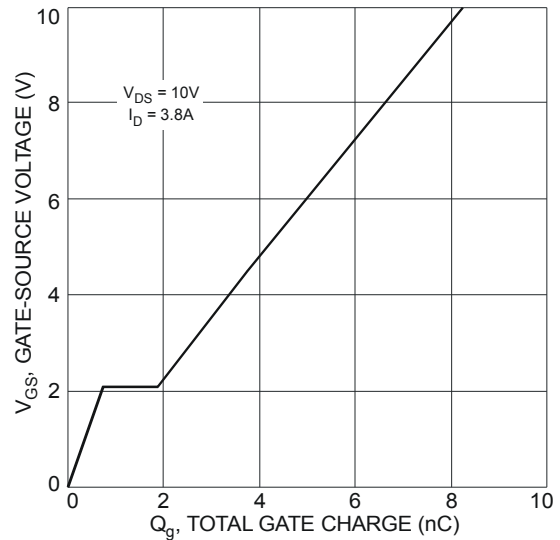
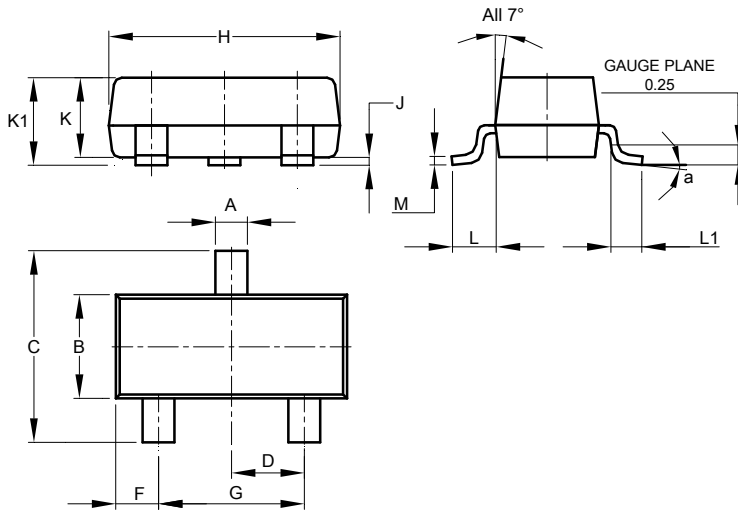


Fig. 8 Gate-Source Voltage vs. Total Gate Charge

**Package Outline Dimensions**

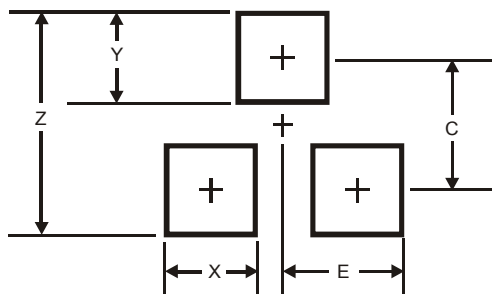
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
α	8°		
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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